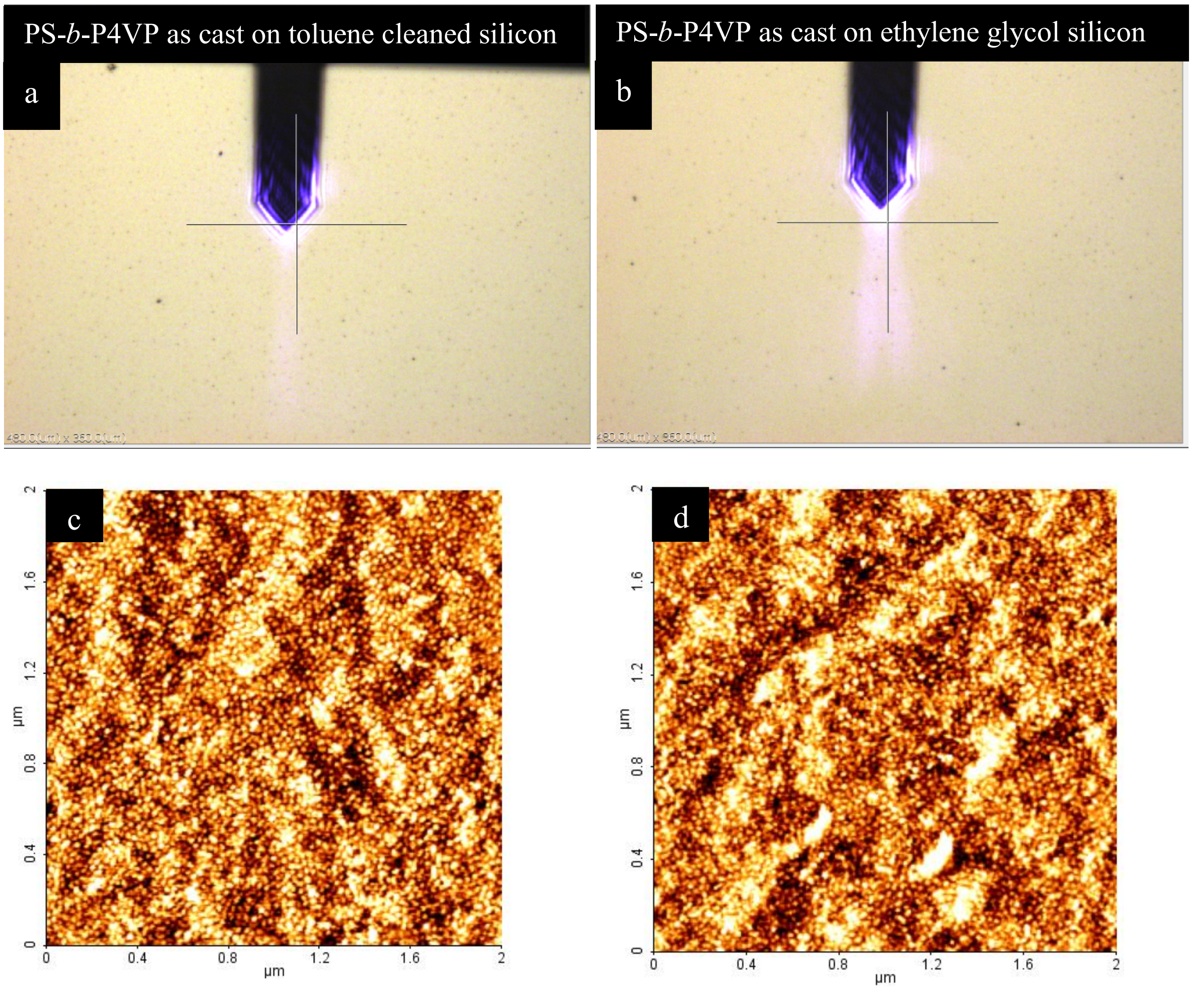
Self-Assembly of Polystyrene-*block*-Poly(4-vinylpyridine) Block Copolymer on Molecularly Functionalized Silicon Substrates: Fabrication of Inorganic Nanostructured Etchmask for Lithographic Use

Supporting Information;


PS-*b*-P4VP as cast on toluene cleaned silicon

PS-*b*-P4VP as cast on ethylene glycol silicon

Fig. S1 Optical images (480 x 360 micron) of (a) PS-*b*-P4VP as cast on toluene cleaned silicon and (b) PS-*b*-P4VP as cast on a silicon oxide surface functionalized with an ethylene glycol layer. (c) and (d) show the corresponding topographic AFM structures.

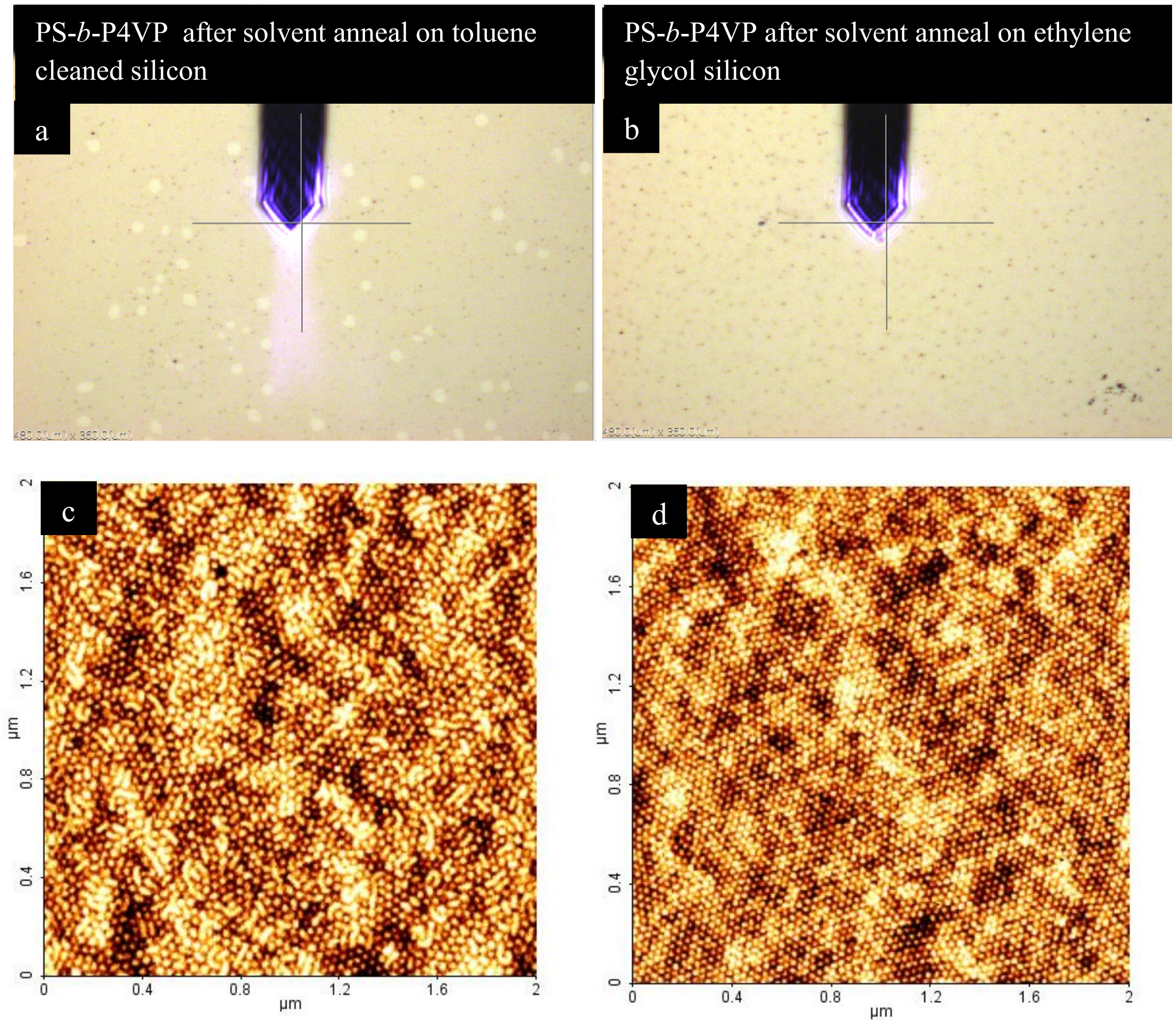


Fig. S2 Optical images (480 x 360 micron) of (a) PS-*b*-P4VP after solvent anneal with THF at 50°C on toluene cleaned silicon and (b) PS-*b*-P4VP after solvent anneal with THF at 50°C on a silicon oxide surface functionalized with an ethylene glycol layer. (c) and (d) show the corresponding topographic AFM structures.